

Description

The HFDN86501LZ uses advanced trench technology to provide excellent $R_{\rm DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

D g S

General Features

 $V_{DS} = 60V I_D = 3A$

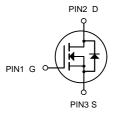
 $R_{DS(ON)}$ < $85m\Omega$ @ V_{GS} =10V

Application

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)	
HFDN86501LZ	SOT-23	S10	3000PCS	

Absolute Maximum Ratings (T_A=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	60	V
Vgs	Gate-Source Voltage	±20	V
Ι _D	Drain Current-Continuous	3	А
Ідм	Drain Current-Pulsed (Note 1)	10	А
Po	Maximum Power Dissipation	1.7	W
Тл,Твтв	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	73.5	°C/W

N-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25°C unless otherwise noted)

Gate-Body Leakage Current	I _{GSS}	V_{GS} =±20 V , V_{DS} =0 V	-	-	±100	nA
On Characteristics (Note 3)	aracteristics (Note 3)					
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=250\mu A$	0.8	1.3	2.0	>
Drain-Source On-State Resistance	D	V_{GS} =10V, I_D =3A	-	72	85	$m\Omega$
	R _{DS(ON)}	V _{GS} =4.5V, I _D =1.5A	-	85	103	$m\Omega$
Forward Transconductance	g FS	V _{DS} =15V,I _D =2A	-	3	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C _{lss}	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	510	-	PF
Output Capacitance	C _{oss}		-	34	-	PF
Reverse Transfer Capacitance	C _{rss}	F-1.0WI1Z	-	26	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t _{d(on)}		-	6	-	nS
Turn-on Rise Time	t _r	V_{DD} =30V, I_{D} =1.5A	-	15	-	nS
Turn-Off Delay Time	t _{d(off)}	V_{GS} =10 V , R_{GEN} =1 Ω	-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg	\/ -20\/ -24	-	7.5	-	nC
Gate-Source Charge	Q _{gs}	$V_{DS}=30V,I_{D}=3A,$	-	1.4	-	nC
Gate-Drain Charge	Q_{gd}	V _{GS} =4.5V	-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- **2.** Surface Mounted on FR4 Board, $t \le 10$ sec.
- **3.** Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

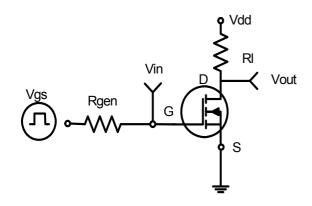
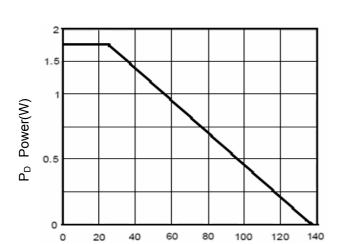


Figure 1:Switching Test Circuit



T_J-Junction Temperature(°C) **Figure 3 Power Dissipation**

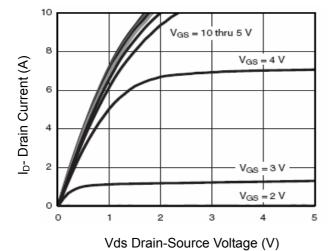


Figure 5 Output Characteristics

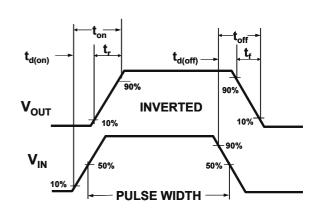


Figure 2:Switching Waveforms

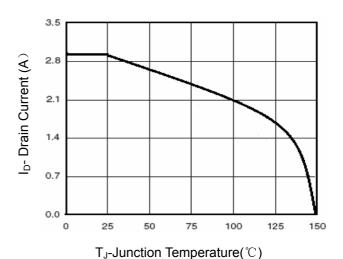


Figure 4 Drain Current

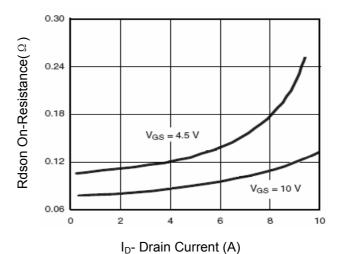


Figure 6 Drain-Source On-Resistance



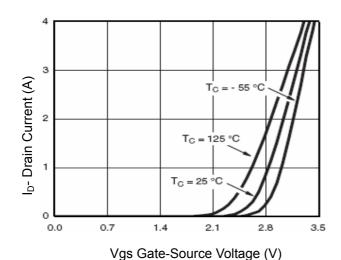
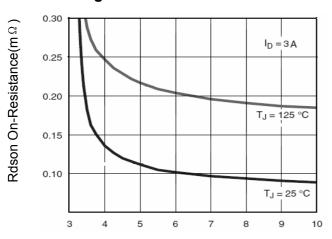
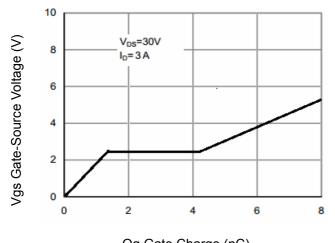


Figure 7 Transfer Characteristics



Vgs Gate-Source Voltage (V)

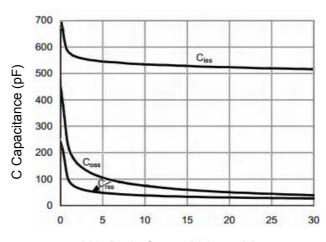
Figure 9 Rdson vs Vgs



Qg Gate Charge (nC) Figure 11 Gate Charge

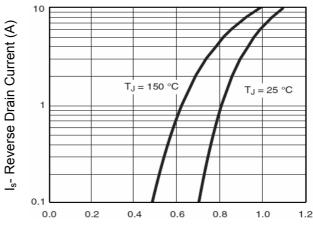
2.0 V_{GS} = 10 V, I_D = 3A V_{GS} = 4.5 V, I_D = 3A V_{GS} = 4.5 V, I_D = 3A V_{GS} = 4.5 V, I_D = 3A V_{GS} = 50 - 25 0 25 50 75 100 125 150

 T_J -Junction Temperature(°C) Figure 8 Drain-Source On-Resistance



Vds Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Vsd Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward



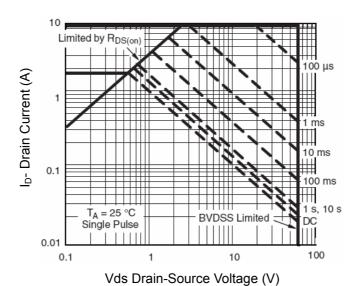


Figure 13 Safe Operation Area

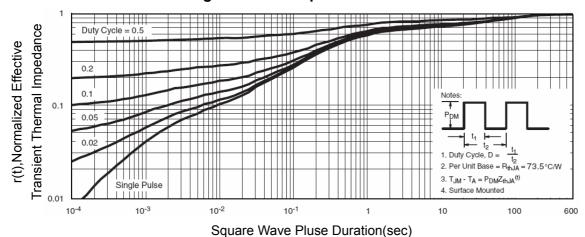
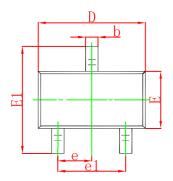
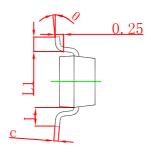
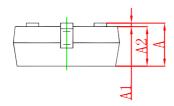


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-23 Package Outline Dimensions

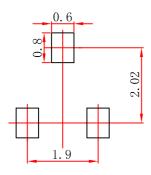






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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